



## 8 BIT ADDRESSABLE LATCH

- SERIAL DATA INPUT - ACTIVE PARALLEL OUTPUT
- STORAGE REGISTER CAPABILITY - MASTER CLEAR
- CAN FUNCTION AS DEMULTIPLEXER
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTER
- 100% TESTED FOR QUIESCENT CURRENT AT 20V
- MAXIMUM INPUT CURRENT OF  $1\mu A$  AT 18V (full package-temperature range),  $100nA$  AT 18V AND  $25^\circ C$
- NOISE MARGIN (full package-temperature range) = 1V AT  $V_{DD} = 5V$ , 2V AT  $V_{DD} = 10V$ , 2.5V AT  $V_{DD} = 15V$
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, " STANDARD SPECIFICATIONS FOR DESCRIPTION OF 'B' SERIES CMOS DEVICES "

### APPLICATION

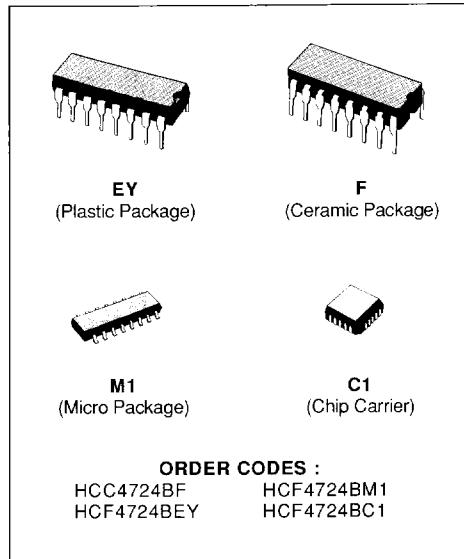
- MULTI-LINE DECODERS
- A/D CONVERTERS

### DESCRIPTION

The HCC/HCF4724B 8-bit addressable latch is a serial-input, parallel-output storage register that can perform a variety of functions.

Data are inputted to a particular bit in the latch when that bit is addressed (by means of inputs A0, A1, A2) and when WRITE DISABLE is at low level. When WRITE DISABLE is high, data entry is inhibited however, all 8 outputs can be continuously read independent of WRITE DISABLE and address inputs.

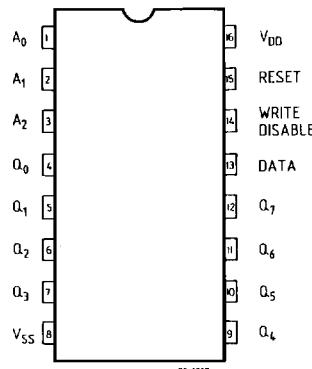
A master RESET input is available, which resets all bits to a logic "0" level when RESET and WRITE DISABLE are at a high level. When RESET is at a high level, and WRITE DISABLE is at a low level, the latch acts as a 1-of-8 demultiplexer ; the bit that is addressed has an active output which follows the data input, while all unaddressed bits are held to a logic "0" level.



### ORDER CODES :

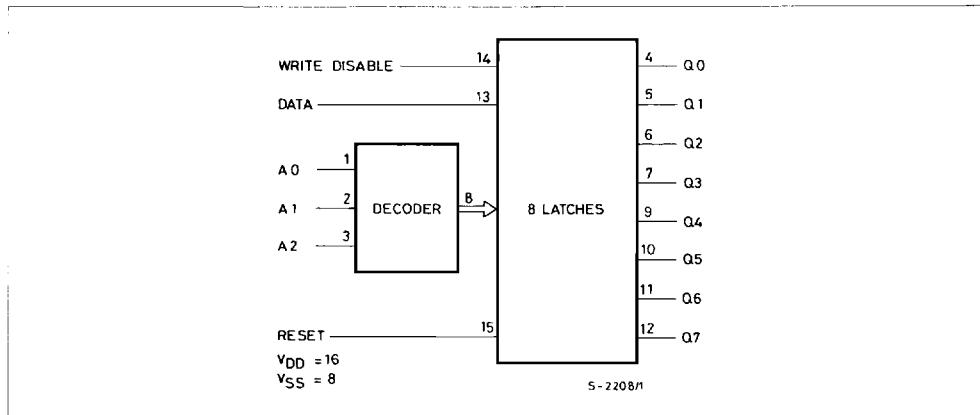
HCC4724BF      HCF4724BM1  
HCF4724BEY      HCF4724BC1

### PIN CONNECTIONS



SC-6387

## FUNCTIONAL DIAGRAM



## ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V <sub>DD</sub> *	Supply Voltage: <b>HCC Types</b> <b>HCF Types</b>	-0.5 to +20 -0.5 to +18	V
V <sub>I</sub>	Input Voltage	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>I</sub>	DC Input Current (any one input)	± 10	mA
P <sub>TOT</sub>	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200 100	mW
T <sub>OP</sub>	Operating Temperature: <b>HCC Types</b> <b>HCF Types</b>	-55 to +125 -40 to +85	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

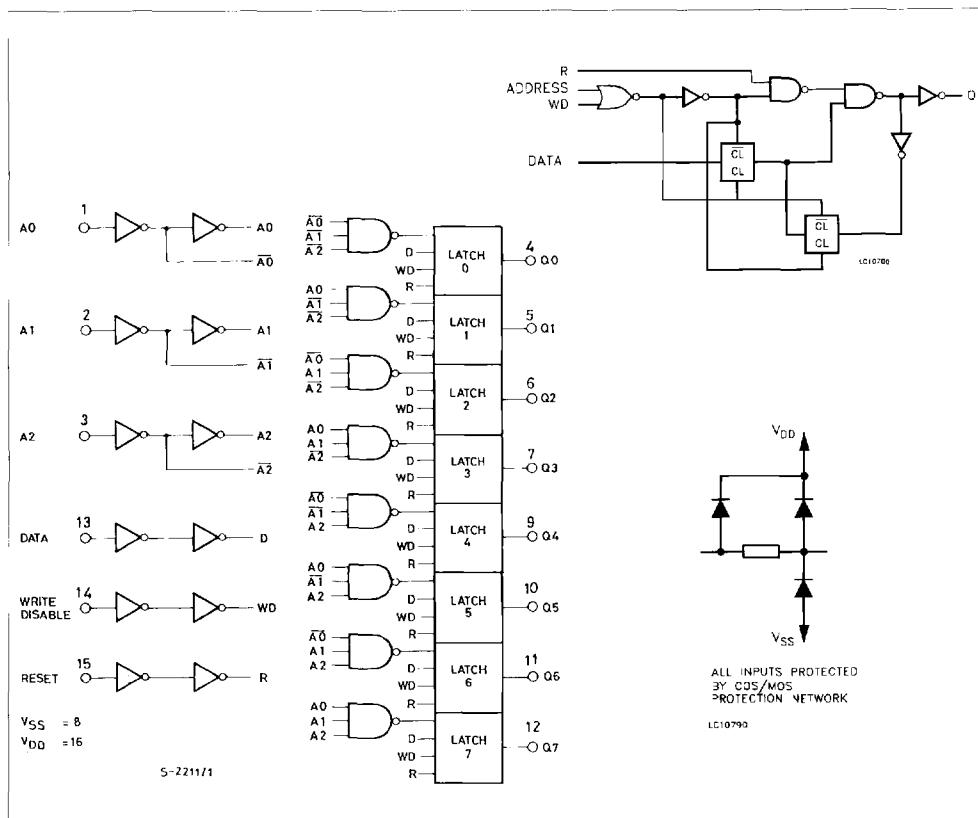
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

\* All voltage values are referred to V<sub>SS</sub> pin voltage.

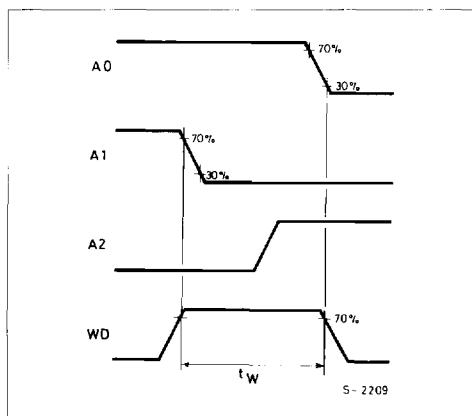
## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage: <b>HCC Types</b> <b>HCF Types</b>	3 to 18 3 to 15	V
V <sub>I</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>OP</sub>	Operating Temperature: <b>HCC Types</b> <b>HCF Types</b>	-55 to +125 -40 to +85	°C

## LOGIC DIAGRAM



## Definition of WRITE DISABLE ON Time



## MODE SELECTION

TYPE	WD	R	Addressed Latch	Unaddressed Latch
A	0	0	Follows Data	Hold Previous State
B	0	1	Follows Data (Active High 8-Channel De- multiplexer)	Reset to "0"
C	1	0	Hold Previous State	
D	1	1	Reset to "0"	Reset to "0"

WD = WRITE DISABLE R = RESET

## STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

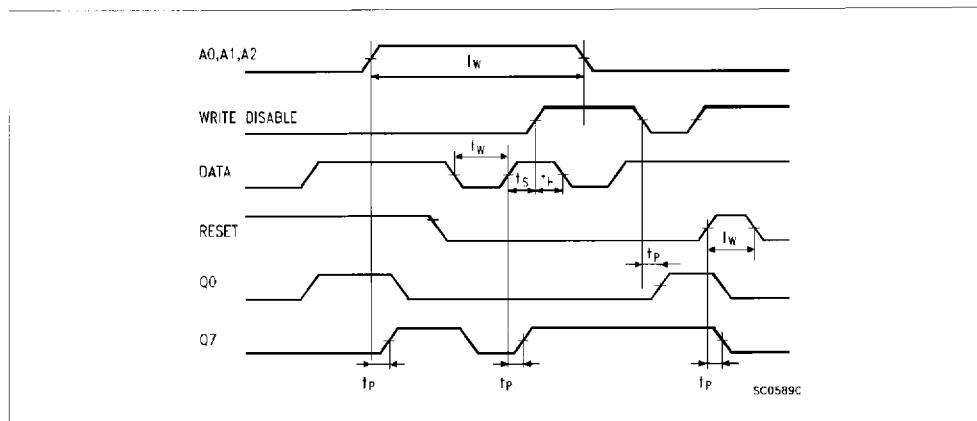
Symbol	Parameter	Test Conditions				Value						Unit			
		V <sub>I</sub> (V)	V <sub>O</sub> (V)	I <sub>O</sub>   (μA)	V <sub>DD</sub> (V)	T <sub>LOW</sub> *		25 °C			T <sub>HIGH</sub> *				
						Min.	Max.	Min.	Typ.	Max.	Min.	Max.			
I <sub>L</sub>	Quiescent Current	HCC Types	0/5		5		5		0.04	5		150	μA		
			0/10		10		10		0.04	10		300			
			0/15		15		20		0.04	20		600			
			0/20		20		100		0.08	100		3000			
			HCF Types	0/5	5		20		0.04	20		150			
		HCF Types	0/10		10		40		0.04	40		300	mA		
			0/15		15		80		0.04	80		600			
			V <sub>OH</sub>	Output High Voltage	0/5	< 1	5	4.95		4.95		4.95		V	
			0/10		< 1	10	9.95		9.95			9.95			
			0/15		< 1	15	14.95		14.95			14.95			
V <sub>OL</sub>	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05		V	
		10/0		< 1	10		0.05			0.05		0.05			
		15/0		< 1	15		0.05			0.05		0.05			
V <sub>IH</sub>	Input High Voltage	0.5/4.5	< 1	5	3.5			3.5			3.5			V	
		1/9	< 1	10	7			7			7				
		1.5/13.5	< 1	15	11			11			11				
V <sub>IL</sub>	Input Low Voltage	4.5/0.5	< 1	5		1.5			1.5		1.5			V	
		9/1	< 1	10		3			3		3				
		13.5/1.5	< 1	15		4			4		4				
I <sub>OH</sub>	Output Drive Current	HCC Types	0/5	2.5	5	-2		-1.6	-3.2		-1.15			mA	
			0/5	4.6	5	-0.64		-0.51	-1		-0.36				
			0/10	9.5	10	-1.6		-1.3	-2.6		-0.9				
			0/15	13.5	15	-4.2		-3.4	-6.8		-2.4				
		HCF Types	0/5	2.5	5	-1.8		-1.6	-3.2		-1.3				
			0/5	4.6	5	-0.61		-0.51	-1		-0.42				
			0/10	9.5	10	-1.5		-1.3	-2.6		-1.1				
			0/15	13.5	15	-4		-3.4	-6.8		-2.8				
			V <sub>OL</sub>	Output Sink Current	0/5	0.4	5	0.64	0.51	1		0.36			mA
		HCC Types	0/10	0.5	10	1.6		1.3	2.6			0.9			
			0/15	1.5	15	4.2		3.4	6.8			2.4			
		HCF Types	0/5	0.4	5	0.61		0.51	1			0.42			
			0/10	0.5	10	1.5		1.3	2.6			1.1			
			0/15	1.5	15	4		3.4	6.8			2.8			
I <sub>IH</sub> , I <sub>IL</sub>	Input Leakage Current	0/18	Any Input	18		±0.1		±10 <sup>-5</sup>	±0.1		±1	μA			
C <sub>I</sub>	Input Capacitance		Any Input					5	7.5			pF			

\* T<sub>LOW</sub> = -55 °C for HCC device; -40 °C for HCF device.\* T<sub>HIGH</sub> = +125 °C for HCC device; +85 °C for HCF device.The Noise Margin for both "1" and "0" level is: 1V min. with V<sub>DD</sub> = 5 V, 2 V min. with V<sub>DD</sub> = 10 V, 2.5 V min. with V<sub>DD</sub> = 15 V

**DYNAMIC ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25^{\circ}\text{C}$ ,  $C_L = 50 \text{ pF}$ ,  $R_L = 200 \text{ k}\Omega$ , typical temperature coefficient for all  $V_{DD}$  values is  $03\%/\text{ }^{\circ}\text{C}$ , all input rise and fall times= 20 ns)

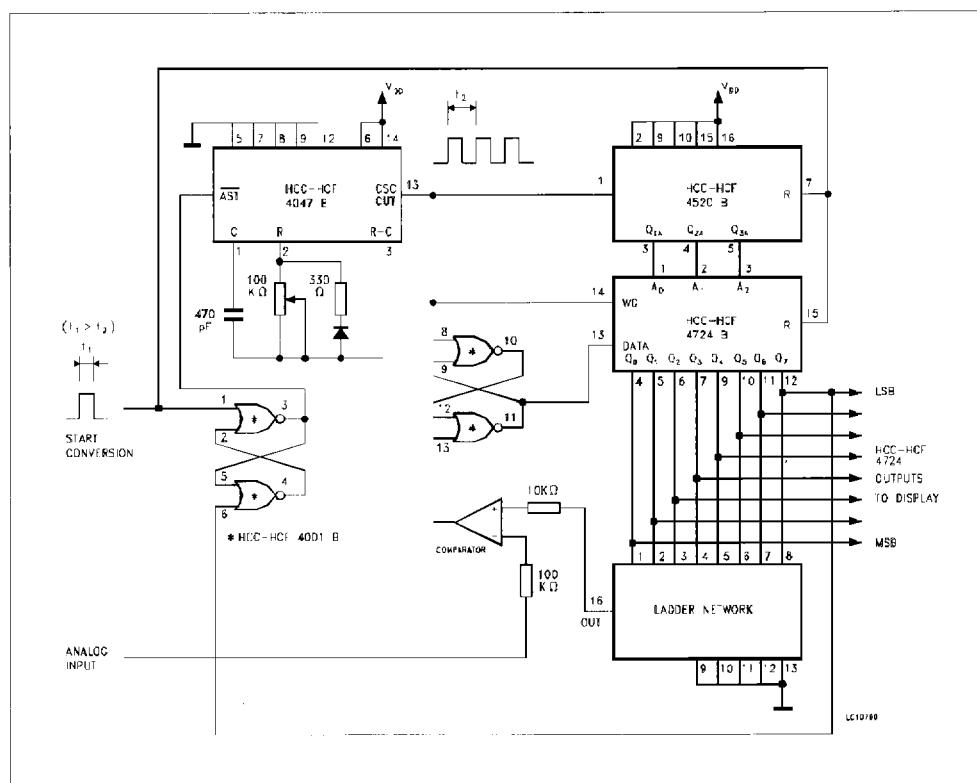
Symbol	Parameter	Test Conditions			Value	Unit
		$V_{DD}$ (V)	Min.	Typ.	Max.	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time Data to Output	(See Figure 1)	5	200	400	ns
			10	75	150	
			15	50	100	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time Write Disable to Output	(See Figure 1)	5	200	400	ns
			10	80	160	
			15	60	120	
$t_{PHL}$	Propagation Delay Time Reset to Output	(See Figure 1)	5	175	350	ns
			10	80	160	
			15	65	130	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time Address to Output	(See Figure 1)	5	225	450	ns
			10	100	200	
			15	75	150	
$t_{TLH}$ $t_{THL}$	Transition Time Any Output		5	100	200	ns
			10	50	100	
			15	40	80	
$t_w$	Minimum Pulse Width Data	(See Figure 1)	5	100	200	ns
			10	50	100	
			15	40	80	
	Minimum Pulse Width Address	(See Figure 1)	5	200	400	ns
			10	100	200	
			15	65	125	
	Minimum Pulse Width Reset	(See Figure 1)	5	75	150	ns
			10	40	75	
			15	25	50	
$t_s$	Minimum Setup Time Data to Write Disable	(See Figure 1)	5	50	100	ns
			10	25	50	
			15	20	35	
$t_h$	Minimum Hold Time Data to Write Disable	(See Figure 1)	5	75	150	ns
			10	40	75	
			15	25	50	
$C_{IN}$	Input Capacitance		Any Input	5	7.5	pF

Figure 1: Master Timing Diagram

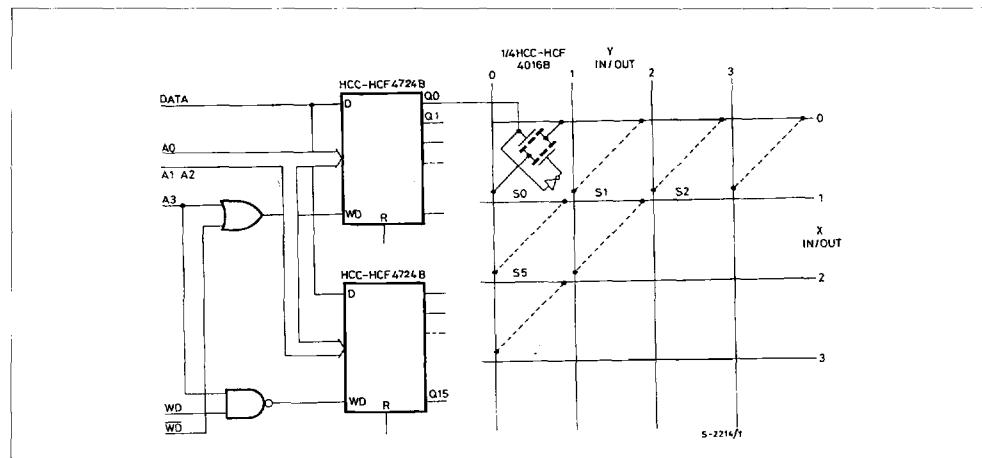


## TYPICAL APPLICATIONS

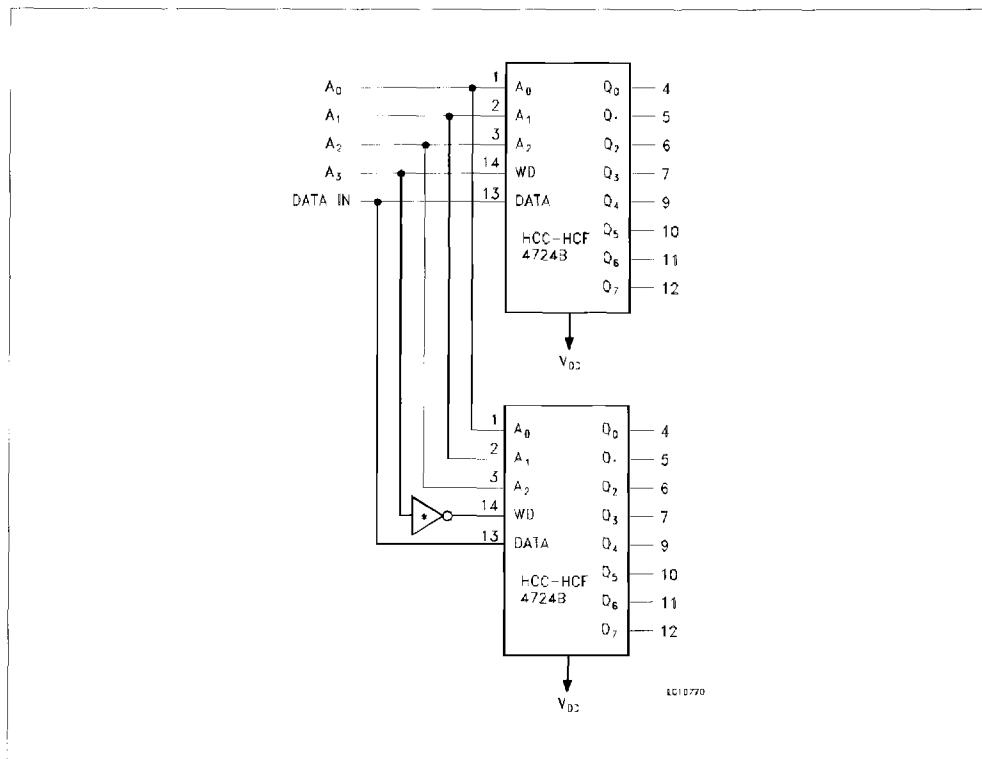
## A/D Converter



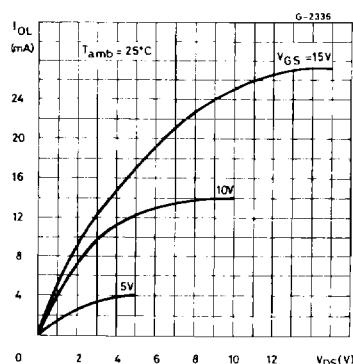
## Multiple Selection Decoding - 4 x 4 Crosspoint Switch



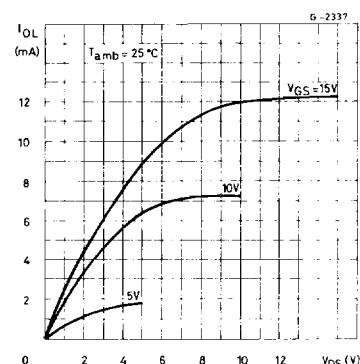
## 1 of 6 Decoder/Demultiplexer



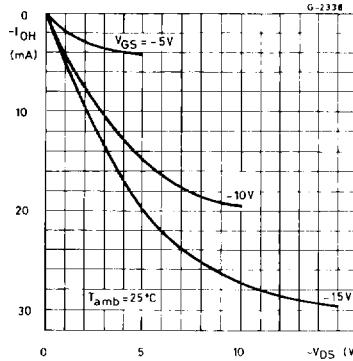
Typical Output Low (sink) Current Characteristics



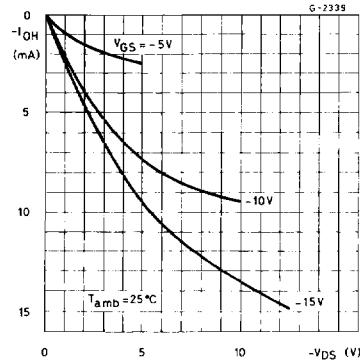
Minimum Output Low (sink) Current Characteristics



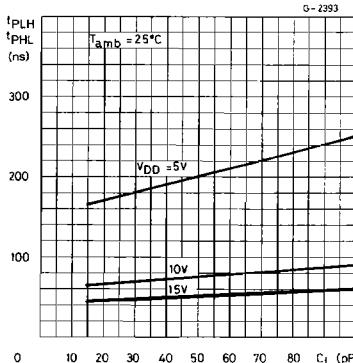
Typical Output High (source) Current Characteristics



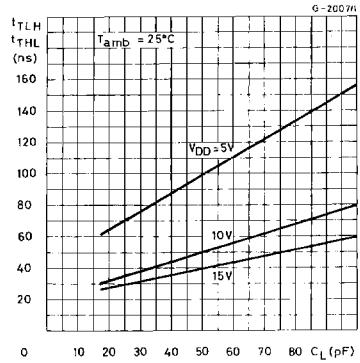
Minimum Output High (source) Current Characteristics



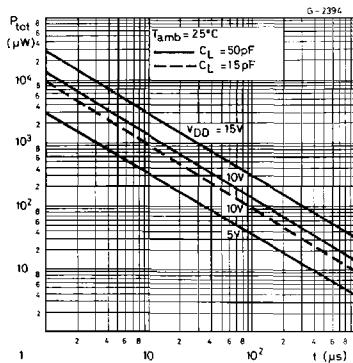
Typical Propagation Delay Time (data to Qn) vs Load Capacitance



Typical Transition Time vs Load Capacitance

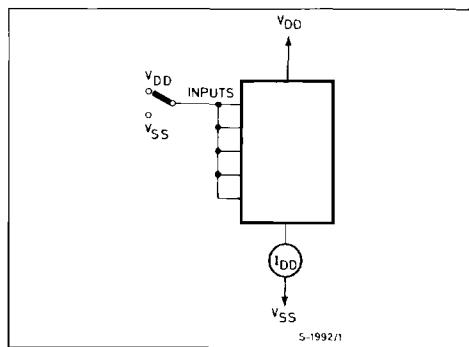


Typical Dynamic Power Dissipation vs Address Cycle Time

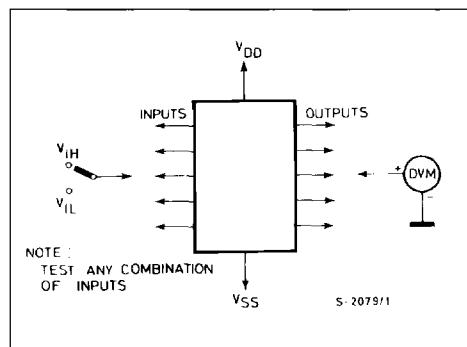


## TEST CIRCUITS

Quiescent Device Current.



Noise Immunity.



Input Leakage Current.

